

#### **Features:**

- 650V Schottky Diode •
- Zero Reverse Recovery Current .
- High Frequency Operation •
- Positive Temperature Coefficient •
- Temperature independent • Switching

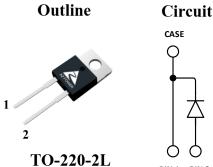
# **Applications:**

- Switch Mode Power Supply •
- Booster diodes in PFC, DC/DC •
- AC/DC converters

## **Benefits:**

- Unipolar Rectifier •
- Minimal switching loss •
- Higher Efficiency •
- Low cooling requirement •

Symbol	Value	Unit		
V <sub>RRM</sub>	650	V		
$I_F \ (Tc = 145^{\circ}C)$	15	А		
Qc	32	nC		



ult	UI
	CASE
	Q
]	T T
+	
T`	
С	0
PIN 2	PIN 1

Symbol	Parameter	Value	Unit	<b>Test Conditions</b>
V <sub>R</sub>	DC Peak Reverse Voltage	650	V	$T_J = 25^{\circ}C$
V <sub>RRM</sub>	Repetitive Peak Reverse	650	V	$T_J = 25^{\circ}C$
V <sub>RSM</sub>	Surge Peak Reverse Voltage	650	V	$T_J = 25^{\circ}C$
I <sub>F</sub>	Continuous Forward Current	42 19 15	А	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 135^{\circ}{\rm C}$ $T_{\rm C} = 145^{\circ}{\rm C}$
IFRM	Repetitive Peak Forward Surge Current	88 79	А	$T_{\rm C}$ =25°C, $T_{\rm P}$ =10ms, Half Sine Wave Tc=125°C, $T_{\rm P}$ =10ms, Half Sine Wave
I <sub>FSM</sub>	Non-Repetitive Peak Forward Surge Current	119 107	А	$T_{\rm C}$ =25°C, $T_{\rm P}$ = 10ms, Half Sine Wave Tc = 125°C, $T_{\rm P}$ = 10ms, Half Sine Wave
PD	Power Dissipation	150 50	W	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 125^{\circ}{\rm C}$
T <sub>J,max</sub>	Operating Junction Temperature	175	°C	
T <sub>stg</sub>	Storage Temperature Range	-55 to 175	°C	
S2D065V015A_Rev_1.0				

### **Maximum Ratings**

S2D065V015A, Rev. 1.0

Page 1 of 4



## Thermal characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit
RthJC	Thermal resistance		1.0		°C/W

### **Electrical Characteristics**

Symbol	Dovometer	Value		Unit	Test Conditions		
Symbol	Parameter	Min. Typ. Max.					
VDC	DC Blocking Voltage	650			V	$I_R = 100 \mu A, T_J = 25^{\circ}C$	
V <sub>F</sub>	Forward Voltage		1.55	1.8	v	$I_F = 15A, T_J = 25^{\circ}C$	
▼ F	rorward vonage		1.9	2.2		$I_F = 15A, T_J = 175^{\circ}C$	
I <sub>R</sub>	Reverse Current		5	100	μΑ	$V_{R} = 650V, T_{J} = 25^{\circ}C$	
IR	Reverse Current		10	250		$V_R = 650V, T_J = 175^{\circ}C$	
	Total Courseiting Channel		32 nC		0	C	$I_F = 15A, dI/dt = 350A/\mu s$
QC	Total Capacitive Charge			nC	$T_J = 25^{\circ}C, V_R = 400V$		
			702			$V_{R} = 1V, T_{J} = 25^{\circ}C, f = 1 \text{ MHz}$	
С	Total Capacitance94pF9393	pF	$V_R$ =200V, $T_J$ =25°C, f=1 MHz				
			93			$V_R$ =400V, $T_J$ =25°C, f=1 MHz	

### **Typical Performance**

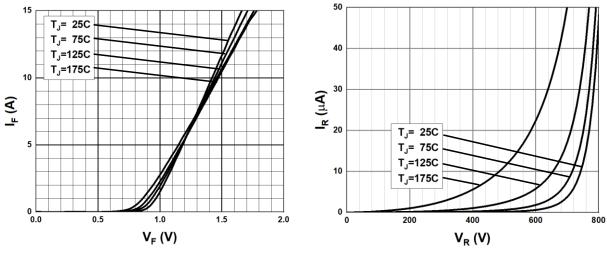
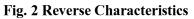


Fig. 1 Forward Characteristics



0



**Typical Performance** 

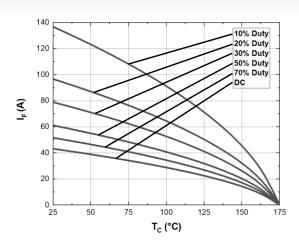


Fig. 3 Current Derating

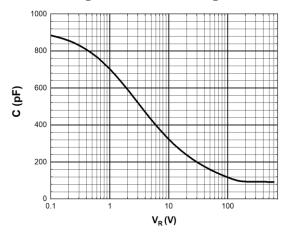


Fig. 5 Capacitance vs. Reverse Voltage

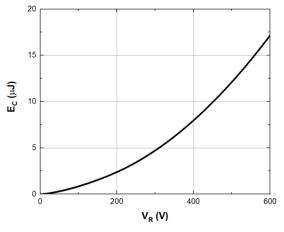


Fig. 7 Capacitance stored Energy

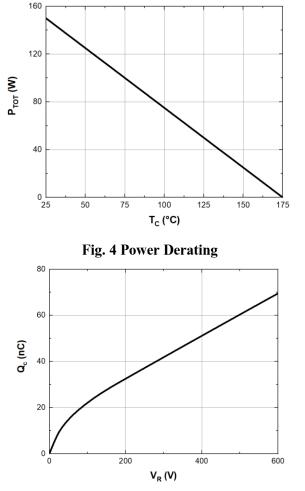
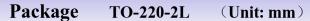


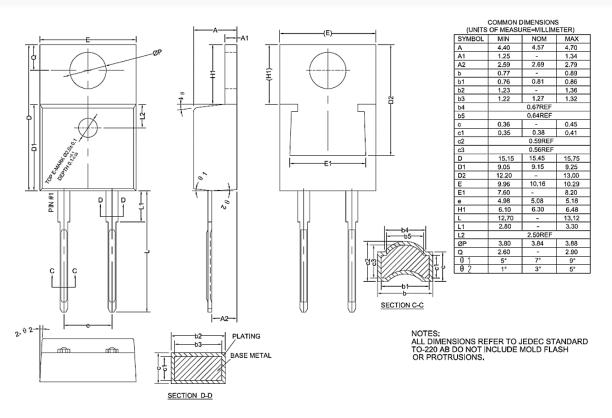
Fig. 6 Recovery Charge vs. Reverse Voltage

S2D065V015A, Rev. 1.0

Page 3 of 4







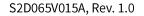
This Product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, systems, or air-traffic control systems.

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, AZ Power Inc. disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.



5601 W SLAUSON AVE 190 CULVER CITY, CA 90230 WWW.AZPE.COM

Information in this document may change without notice. All referenced product or service names and trademarks are the property of their respective owners. Copyright © 2020 AZ Power Inc. All rights reserved.



Page 4 of 4

0